PBSS4021NX 20 V, 7 A NPN Iow VCEsat (BISS) transistor 11 December 2012

Product data sheet

### 1. General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PX.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	20	V	
I <sub>C</sub>	collector current			-	-	7	А	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	15	А	
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 5 A; $I_{B}$ = 500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C		-	19	28	mΩ	

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3
3	В	base	3 2 1 SOT89	sym042

### 6. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
PBSS4021NX	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

### 7. Marking

Table 4.     Marking codes	
Type number	Marking code
	[1]
PBSS4021NX	%6D

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	20	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	15	А
I <sub>B</sub>	base current			-	1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	600	mW
			[2]	-	1650	mW
			[3]	-	2500	mW
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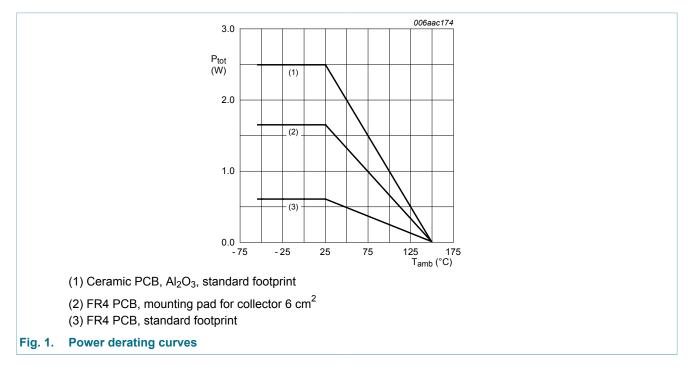
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Symbol	Parameter	Conditions	Min	Мах	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.



### 9. Thermal characteristics

Table 6.     Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
f	thermal resistance from junction to ambient	in free air	[1]	-	-	210	K/W	
			[2]	-	-	75	K/W	
			[3]	-	-	50	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

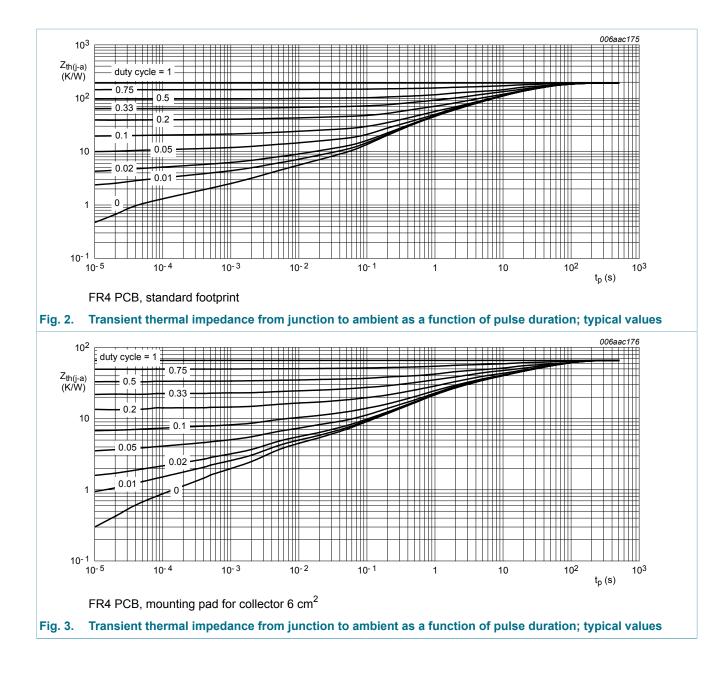
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

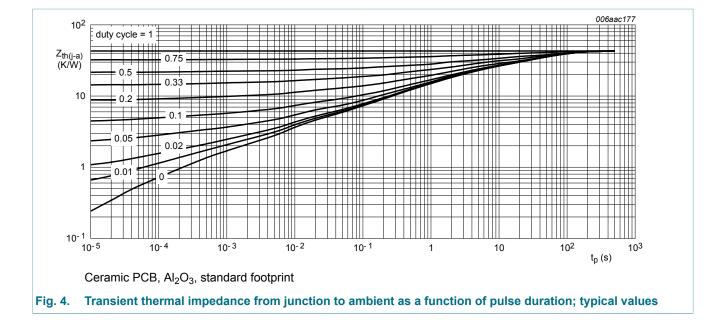
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### **10. Characteristics**

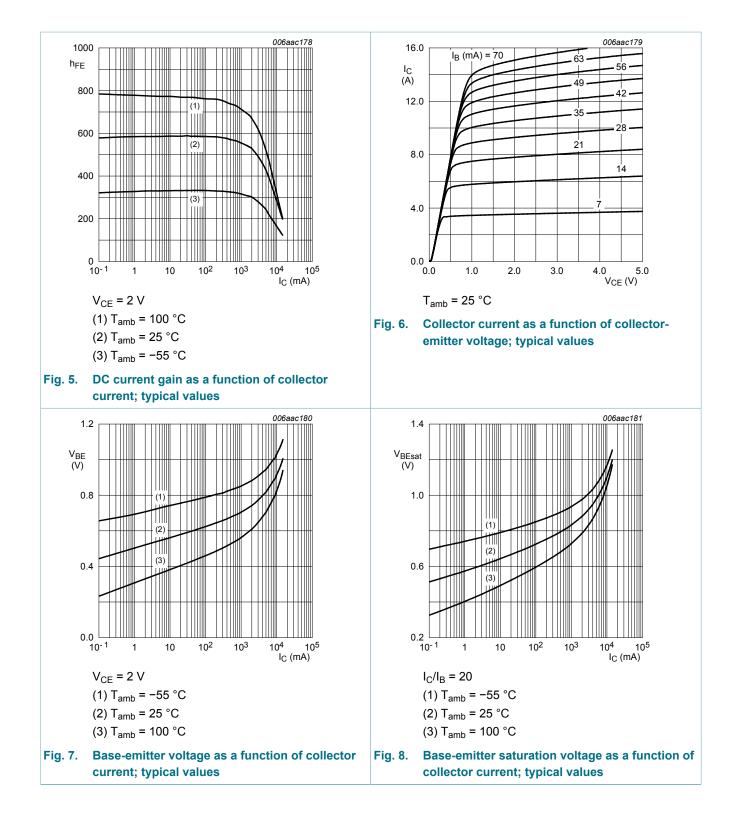
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 16 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 \text{ V; } I_C = 500 \text{ mA; pulsed;}$ $t_p \le 300  \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	300	550	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \text{ V; } I_C = 1 \text{ A; pulsed; } t_p \leq 300  \mu\text{s;} \\ \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{split}$	300	550	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \leq 300  \mu\text{s;} \\ \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{split}$	300	500	-	
		$V_{CE} = 2 \text{ V; } I_C = 4 \text{ A; pulsed; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	250	450	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} \texttt{= 2 V; I}_{C} \texttt{= 8 A; pulsed; t}_{p} \texttt{\leq 300 } \texttt{\mu s;} \\ \delta \texttt{\leq 0.02 ; T}_{amb} \texttt{= 25 °C} \end{array}$	100	200	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	25	38	mV
		$I_{C}$ = 1 A; $I_{B}$ = 10 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	35	60	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_{C}$ = 2 A; $I_{B}$ = 40 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	48	75	mV
		$I_{C}$ = 4 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	78	120	mV
		$I_C$ = 4 A; $I_B$ = 40 mA; pulsed; $t_p \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	85	140	mV
		$I_C$ = 7 A; $I_B$ = 350 mA; pulsed; $t_p \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	137	210	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_C &= 5 \text{ A};  I_B = 500 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02 ;  T_{amb} = 25 ^\circ\text{C} \end{split}$	-	19	28	mΩ
DEGU	base-emitter saturation voltage	$\begin{split} I_{C} &= 1 \text{ A};  I_{B} = 100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02 \text{ ; }  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	0.82	0.9	V
		$I_{C}$ = 4 A; $I_{B}$ = 400 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	0.92	1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$\label{eq:Vce} \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 2 A; pulsed; } t_{p} \texttt{\leq 300 } \mu s; \\ \bar{d} \texttt{\leq 0.02 ; } T_{amb} \texttt{= 25 °C} \end{array}$	-	0.74	0.85	V
t <sub>d</sub>	delay time	$V_{CC}$ = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	40	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	40	-	ns
t <sub>on</sub>	turn-on time		-	80	-	ns
t <sub>s</sub>	storage time	-	-	650	-	ns
t <sub>f</sub>	fall time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	75	-	ns
t <sub>off</sub>	turn-off time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	725	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	115	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	85	-	pF

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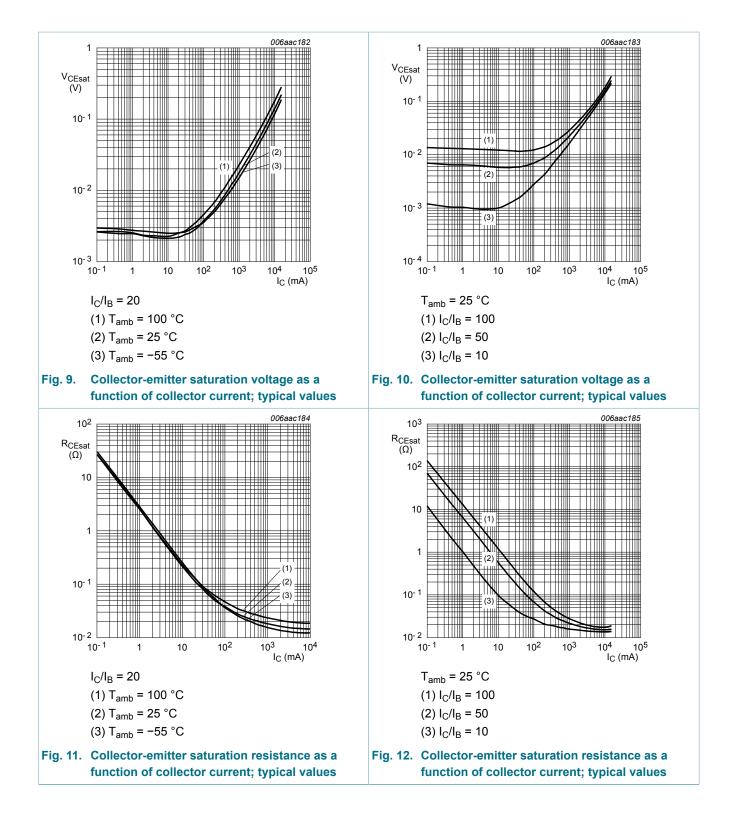


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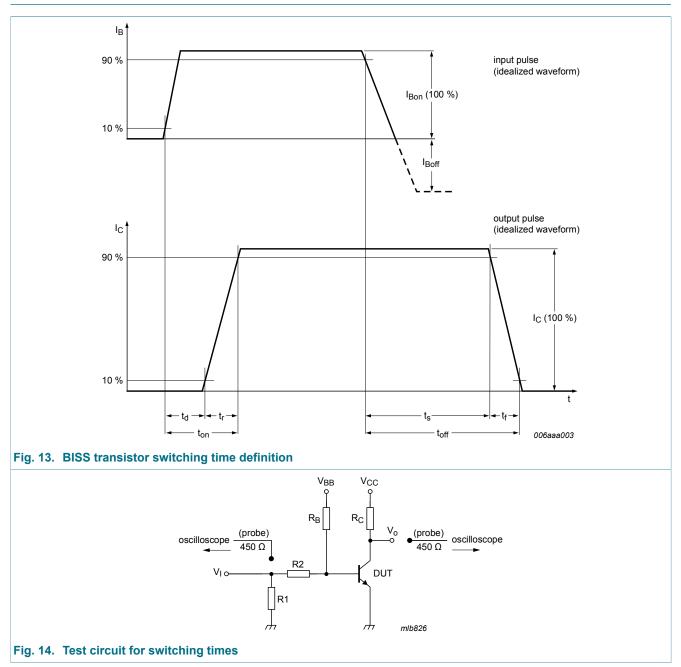
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### **11. Test information**

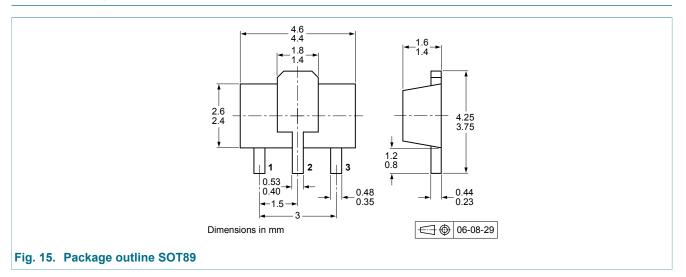
#### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

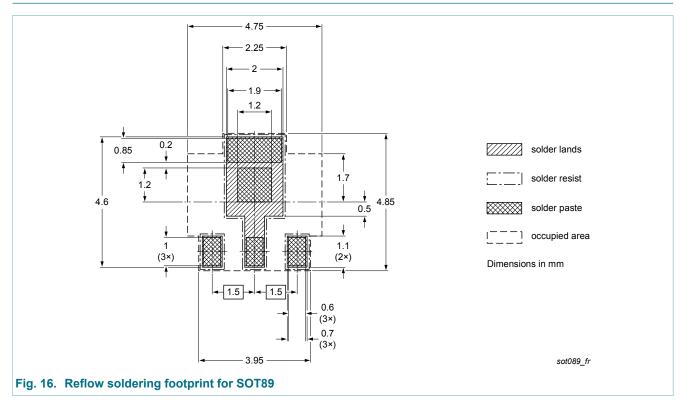
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### 12. Package outline

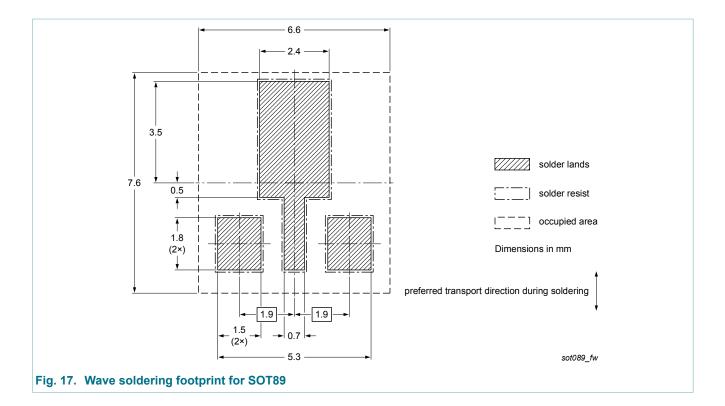


### 13. Soldering



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### 14. Revision history

Table 8. Revision h	nistory			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NX v.3	20121211	Product data sheet	-	PBSS4021NX v.2
Modifications:	Editorial update	·		,
PBSS4021NX v.2	20121009	Product data sheet	-	PBSS4021NX v.1
PBSS4021NX v.1	20100401	Product data sheet	-	-

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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